State-of-the-Art Program on Compound Semiconductors 51 (SOTAPOCS 51) -and- Wide-Bandgap Semiconductor Materials and Devices 10

Editors:

E. Stokes
The University of North Carolina at Charlotte
Charlotte, North Carolina, USA

R. Goldhahn
Technical University of Ilmenau
Ilmenau, Germany

G. Hunter
NASA Glenn Research Center
Cleveland, Ohio, USA

C. O'Dwyer
The University of Limerick
Limerick, Ireland

O. Ambacher
Fraunhofer Institute for
Applied Solid State Physics IAF
Freiburg, Germany

J. Huang
National Taiwan University
Taipei City, Taiwan

E. Kohn
University of Ulm
Ulm, Germany

M. E. Overberg
Sandia National Labs
Albuquerque, New Mexico, USA

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